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**B.Tech.**  
**(SEM VII) ODD SEMESTER THEORY EXAMINATION, 2015-16**  
**VLSI DESIGN**

*Time: 3 Hours**Maximum Marks:100*

**Note:** *Attempt all questions.*  
*All questions carry equal marks*

**Q.1. Write a short notes on any two of the following** **10X2**

- (a) VLSI design methodology (Y Chart) & MOS Scaling
- (b) Write short notes on CAD Tools for VLSI Design & Enlist the classification of static CMOS digital logic families
- (c) Discuss the layout design process of CMOS inverter. Draw a stick diagram of CMOS NOR gate.

**Q.2. Attempt any two parts of the following** **10X2**

- (a) Consider a CMOS inverter circuits with the following parameters  $V_{DD} = 3.3V$ ,  $V_{Ton} = 0.6V$ ,  $V_{Top} = -0.7V$ ,  $k_n = 200\mu A/V^2$ ,  $k_p = 80\mu A/V^2$ ,  $k_R = 2.5$  Calculate the noise margin of the circuits.
- (b) Consider a CMOS inverter, with the following device parameters,  $V_{DD} = 3.V$ ,  $V_{Ton} = 0.6V$ ,  $V_{Top} = -0.7V$ ,  $\mu_n C_{ox} = 60\mu A/V^2$ ,  $\mu_p C_{ox} = 20\mu A/V^2$ ,  $\lambda = 0$ . Determine the  $\left(\frac{W}{L}\right)$  ratios of the nMOS and the pMOS transistors such that the switching threshold is  $V_{th} = 1.5V$ .
- (c) Design the circuit described by the Boolean function  $Y = \overline{A.(B + C)(D + E)}$  using CMOS logic. Calculate the equivalent CMOS inverter circuit for simultaneous switching of all inputs assuming that  $\left(\frac{W}{L}\right) = 5$  for pMOS transistor and  $\left(\frac{W}{L}\right) = 2$  for all nMOS transistor.

**Q.3. Attempt any two parts of the following** **10X2**

- (a) Discuss the classification of Dynamic CMOS logic families. Discuss the operation of pass transistor in dynamic logic circuit..
- (b) Discuss the operation of five stage Ring Oscillator circuits & determine the oscillation frequency with PDP ( $R_n = 8k\Omega$ ,  $R_p = 24k\Omega$ ,  $C_{outn} = 4.8fF$ ,  $V_{DD} = 5V$ ).
- (c) Estimate the intrinsic propagation delay  $t_{PHL} + t_{PLH}$  of a three-input NOR gate using minimum size transistor ( $R_n = 8k\Omega$ ,  $R_p = 24k\Omega$  and  $C_{outn} = 4.8fF$ ). Estimate the circuit delay also when the gate is driving a load capacitance of 100fF.

**Q.4. Attempt any two parts of the following****10X2**

- (a) Discuss the Elmore Delay. In a CMOS inverter power supply  $V_{DD} = 5V$ , determine the fall time, which is defined as the time elapsed between the time point at which  $V_{out} = V_{90\%} = 4.5V$  and the time point at which  $V_{out} = V_{10\%} = 0.5$ . The output load capacitance is  $1pF$ . The nMOS transistor parameters are as follows:  $V_{Tn} = 1.0V$ ,  $\mu_n C_{ox} = 20\mu A/V^2$ ,  $\left(\frac{W}{L}\right)_n = 10$ .
- (b) Discuss the operation of single stage shift register circuits. Design a D flip-flop using TG CMOS logic circuits
- (c) In a logic Design logic function is  $Z = \overline{(A + B + C + D)(E + F + G)(H + I)}$  implemented with inputs (A,E,H) are high and other inputs are low. Draw a domino CMOS circuits diagram with implements Z.

**Q. 5. Attempt any four parts of the following****5X4**

- (a) Define the terms Controllability and Observability.
- (b) Explain the implementation of Built-In Self Test (BIST) design techniques for VLSI circuit testing.
- (c) Write short notes on Adiabatic CMOS logic.
- (d) Discuss the low power MTCMOS VLSI designs techniques.
- (e) Draw and explain the operation of 6T CMOS SRAM cell circuit.
- (f) Explain the overview of Power Consumption in CMOS logic circuits